

Please make the following changes to the paragraph starting with “Referring to FIG. 1...” on page 15 of the August 29, 2005 Amendment:

Referring to FIG. 1, a cross-section of a part of a carrier device 1 with a raised pedestal 2 is taken through the raised pedestal 2, which was formed for example, by a punching tool during the manufacture of the frame. In the example shown, the height “hp” of the pedestal is about 120 micrometers, and the carrier height “h” is about 250 micrometers. The pedestal height hp may be approximately in a range of from 1/5 to twice the material thickness h of the carrier device 1. Compared to the currently common chip height of about 300 micrometers, this corresponds approximately to a range from 1/10 to 1.5 times this chip height. To be suitable for multiple bonding, the raised pedestal should have a sufficient length and width, for example about 250 micrometers, since for each pad diameter, approximately 35 micrometers plus the necessary pad spacing are needed. Referring to FIG. 2, a top view of a raised pedestal 2 with eight bonding pads 4 is shown. The bonding wires 5 and 6 associated with the bonding pads 4 point in different directions. With this raised pedestal 2, two different chips on the carrier platform 1 may be connected with the latter by multiple bonding.